

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9295	inspect\$3 same clean\$3 same (device\$1 chip die IC (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 10:31
L2	238	1 and ((scan\$4 near electron near microscope) SEM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 10:34
L3	4	2 and (clean\$3 with ((oxygen O2 "O.sub.2") near2 plasma))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 10:45
L4	0	(wafer near product\$3 near (region\$1 area\$1)) with (calibrat\$3 near (region\$1 area\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 10:47
L5	8	(wafer near2 (region\$1 area\$1)) with (calibrat\$3 near (region\$1 area\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 10:52
L6	25	wafer with (conduct\$3 near (layer\$1 film\$1)) with (buffer near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:00
L7	0	(first near conduct\$3 near (layer\$1 film\$1) near2 AlCu) with (second near conduct\$3 near (layer\$1 film\$1) near2 W) with (buffer near (layer film) near2 TiN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:04
L8	0	(first near conduct\$3 near (layer\$1 film\$1) near2 AlCu) same (second near conduct\$3 near (layer\$1 film\$1) near2 W) same (buffer near (layer film) near2 TiN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:03
L9	0	(first near conduct\$3 near (layer\$1 film\$1) near2 AlCu) and (second near conduct\$3 near (layer\$1 film\$1) near2 W) and (buffer near (layer film) near2 TiN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:03

L10	0	(conduct\$3 near (layer\$1 film\$1) near2 (AlCu W)) with (buffer near (layer film) near2 TiN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:04
L11	0	(conduct\$3 near (layer\$1 film\$1) near2 (AlCu W)) and (buffer near (layer film) near2 TiN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:04
L12	6	((conduct\$3 metal) near (layer\$1 film\$1) near2 (AlCu W)) and (buffer near (layer film) near2 TiN)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 11:05

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	0	((microelectronic near device\$1) IC (integrated near circuit\$1)) with ((scan\$4 near electron near microscopy) SEM) with clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:07
L4	88	((microelectronic near device\$1) IC (integrated near circuit\$1)) same ((scan\$4 near electron near microscopy) SEM) same clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:09
L5	0	((microelectronic near device\$1) IC (integrated near circuit\$1)) same ((scan\$4 near electron near microscopy) SEM) same (clean\$3 near5 (plasma near (oxygen O2 "O.sub.2")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:11
L6	5	((microelectronic near device\$1) chip wafer circuit\$1 IC (integrated near circuit\$1)) same ((scan\$4 near electron near microscopy) SEM) same (clean\$3 near5 (plasma near (oxygen O2 "O.sub.2")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:16
L7	2	(inspect\$3 near5 ((scan\$4 near electron near microscopy) SEM)) same (clean\$3 near5 (plasma near (oxygen O2 "O.sub.2")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:18
L8	7	(inspect\$3 near5 ((scan\$4 near electron near microscopy) SEM)) and (clean\$3 near5 (plasma near (oxygen O2 "O.sub.2")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:24
L9	9	(inspect\$3 with ((scan\$4 near electron near microscopy) SEM)) and (clean\$3 with (plasma near (oxygen O2 "O.sub.2")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 20:25
L13	8	inspect\$3 with (device circuit IC (integrated adj circuit) (semiconductor near (chip die))) with (intermediate near stage near (manufactur\$3 process\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 21:07
L14	7	("4265117" "4796432" "5055140" "5422498" "5698852" "5708371" "5772325").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/06 20:46

L15	34	inspect\$3 with (device circuit IC (integrated adj circuit) (semiconductor near (chip die))) and (intermediate near stage near (manufactur\$3 process\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/08/06 21:07
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